



Si3863BDV vs. Si3863DV

Description: Load Switch with Level-Shift
Package: TSOP-6
Pin Out: Identical

Part Number Replacements:

Si3863BDV-T1-E3 Replaces Si3863DV-T1-E3
 Si3863BDV-T1-E3 Replaces Si3863DV-T1

Summary of Performance:

The Si3863BDV is an upgrade to the original Si3863DV; both parts perform identically, including limits to the parametric tables below.

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED)				
Parameter	Symbol	Si3863BDV	Si3863DV	Unit
Input Voltage	V _{IN}	12	12	V
ON/OFF Voltage	V _{ON/OFF}	8	8	
Load Current	Continuous	±2.5	±2.5	A
	Pulsed	±5	±5	
Continuous Intrinsic Diode Conduction	I _S	-1	-1	
Power Dissipation	P _D	0.83	0.83	W
Operating Junction & Storage Temperature Range	T _j & T _{stg}	-55 to 150	-55 to 150	°C
Maximum Junction-to-Ambient	R _{thJA}	150	150	°C/W

SPECIFICATIONS (T _J = 25°C UNLESS OTHERWISE NOTED)									
Parameter	Symbol	Si3863BDV			Si3863DV			Unit	
		Min	Typ	Max	Min	Typ	Max		
OFF Characteristic									
Reverse Leakage Current	I _{FL}			1			1		µA
Diode Forward Voltage	V _{SD}		-0.75	-1		-0.75	-1		V
Dynamic									
Input Voltage Range	V _{IN}	2.5		12	2.5		12		nC
On-Resistance (p-channel) @ 1A	V _{IN} = 4.5 V		0.057	0.075		0.086	0.105		Ω
	V _{IN} = 3.0 V		0.082	0.105		0.105	0.125		Ω
	V _{IN} = 2.5 V		0.110	0.140		0.135	0.165		Ω
On-State (p-channel) Drain-Current	V _{IN} = 10 V	1			1				A
	V _{IN} = 5 V	1			1				A